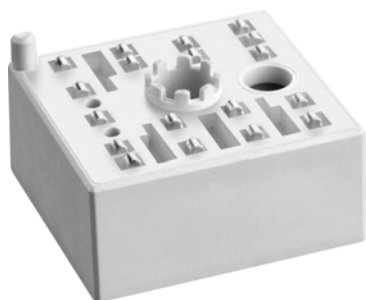


# SKiiP 03NAC12T4V1



MiniSKiiP® 0

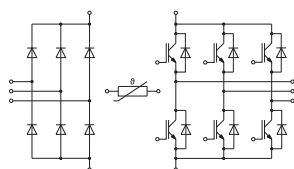
## SKiiP 03NAC12T4V1

### Features\*

- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

### Remarks

- Max. case temperature limited to  $T_C=125^\circ\text{C}$
- Product reliability results valid for  $T_J \leq 150^\circ\text{C}$  (recommended  $T_{J,op} = -40 \dots +150^\circ\text{C}$ )
- Temperature sensor: No basic insulation to main circuit, max. potential difference 850V to -DC

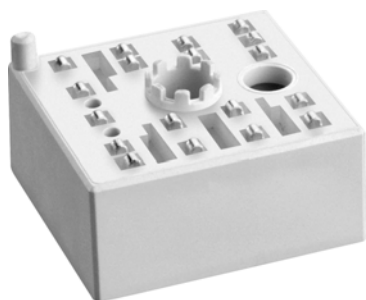


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| Absolute Maximum Ratings |  |                         |             |                  |
|--------------------------|--|-------------------------|-------------|------------------|
| Symbol                   | Conditions   |                         | Values      | Unit             |
| Inverter - IGBT          |  |                         |             |                  |
| V <sub>CES</sub>         | T <sub>j</sub> = 25 °C   |                         | 1200        | V                |
| I <sub>C</sub>           | T <sub>j</sub> = 150 °C  | T <sub>s</sub> = 25 °C  | 7.5         | A                |
|                          |  | T <sub>s</sub> = 70 °C  | 7.5         | A                |
| I <sub>C</sub>           | T <sub>j</sub> = 175 °C  | T <sub>s</sub> = 25 °C  | 7.5         | A                |
|                          |  | T <sub>s</sub> = 70 °C  | 7.5         | A                |
| I <sub>Cnom</sub>        |  |                         | 8           | A                |
| I <sub>CRM</sub>         |  |                         | 24          | A                |
| V <sub>GES</sub>         |  |                         | -20 ... 20  | V                |
| t <sub>psc</sub>         | V <sub>CC</sub> = 800 V<br>V <sub>GE</sub> ≤ 15 V<br>V <sub>CES</sub> ≤ 1200 V | T <sub>j</sub> = 150 °C | 10          | μs               |
| T <sub>j</sub>           |  |                         | -40 ... 175 | °C               |
| Inverse - Diode          |  |                         |             |                  |
| V <sub>RRM</sub>         | T <sub>j</sub> = 25 °C   |                         | 1200        | V                |
| I <sub>F</sub>           | T <sub>j</sub> = 150 °C  | T <sub>s</sub> = 25 °C  | 9           | A                |
|                          |  | T <sub>s</sub> = 70 °C  | 9           | A                |
| I <sub>F</sub>           | T <sub>j</sub> = 175 °C  | T <sub>s</sub> = 25 °C  | 9           | A                |
|                          |  | T <sub>s</sub> = 70 °C  | 9           | A                |
| I <sub>FRM</sub>         |  |                         | 24          | A                |
| I <sub>FSM</sub>         | t <sub>p</sub> = 10 ms, sin 180°, T <sub>j</sub> = 150 °C                      |                         | 36          | A                |
| T <sub>j</sub>           |  |                         | -40 ... 175 | °C               |
| Rectifier - Diode        |  |                         |             |                  |
| V <sub>RRM</sub>         | T <sub>j</sub> = 25 °C   |                         | 1600        | V                |
| I <sub>F</sub>           | T <sub>s</sub> = 25 °C, T <sub>j</sub> = 150 °C                                |                         | 39          | A                |
| I <sub>FSM</sub>         | t <sub>p</sub> = 10 ms<br>sin 180°   | T <sub>j</sub> = 25 °C  | 220         | A                |
|                          |  | T <sub>j</sub> = 150 °C | 200         | A                |
| i <sup>2</sup> t         | t <sub>p</sub> = 10 ms<br>sin 180°   | T <sub>j</sub> = 25 °C  | 242         | A <sup>2</sup> s |
|                          |  | T <sub>j</sub> = 150 °C | 200         | A <sup>2</sup> s |
| T <sub>j</sub>           |  |                         | -40 ... 150 | °C               |
| Module                   |  |                         |             |                  |
| I <sub>t(RMS)</sub>      | T <sub>terminal</sub> = 80 °C, 20 A per spring                                 |                         | t.b.d.      | A                |
| T <sub>stg</sub>         | module without TIM   |                         | -40 ... 125 | °C               |
| V <sub>isol</sub>        | AC sinus 50 Hz, 1 min  |                         | 2500        | V                |

| Characteristics      |  |                         |      |      |      |      |
|----------------------|--|-------------------------|------|------|------|------|
| Symbol               | Conditions   |                         | min. | typ. | max. | Unit |
| Inverter - IGBT      |  |                         |      |      |      |      |
| V <sub>CE(sat)</sub> | I <sub>C</sub> = 8 A                                       | T <sub>j</sub> = 25 °C  |      | 1.85 | 2.10 | V    |
|                      | V <sub>GE</sub> = 15 V<br>chipelevel                       | T <sub>j</sub> = 150 °C |      | 2.25 | 2.45 | V    |
| V <sub>CE0</sub>     | chipelevel   | T <sub>j</sub> = 25 °C  |      | 0.80 | 0.90 | V    |
|                      |  | T <sub>j</sub> = 150 °C |      | 0.70 | 0.80 | V    |
| r <sub>CE</sub>      | V <sub>GE</sub> = 15 V                                     | T <sub>j</sub> = 25 °C  |      | 131  | 150  | mΩ   |
|                      | chipelevel   | T <sub>j</sub> = 150 °C |      | 194  | 206  | mΩ   |
| V <sub>GE(th)</sub>  | V <sub>GE</sub> = V <sub>CE</sub> V, I <sub>C</sub> = 1 mA |                         | 5    | 5.8  | 6.5  | V    |
| I <sub>CES</sub>     | V <sub>GE</sub> = 0 V                                      | T <sub>j</sub> = 25 °C  |      |      | 1    | mA   |
|                      | V <sub>CE</sub> = 1200 V                                   |                         |      | -    |      | mA   |
| C <sub>ies</sub>     | V <sub>CE</sub> = 25 V<br>V <sub>GE</sub> = 0 V            | f = 1 MHz               |      | 0.49 |      | nF   |
| C <sub>oes</sub>     |  | f = 1 MHz               |      | 0.05 |      | nF   |
| C <sub>res</sub>     |  | f = 1 MHz               |      | 0.03 |      | nF   |

# SKiiP 03NAC12T4V1



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## SKiiP 03NAC12T4V1

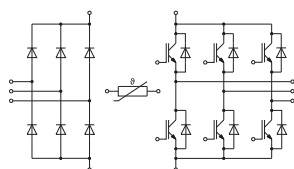
### Features\*

- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

### Remarks

- Max. case temperature limited to  $T_C=125^\circ\text{C}$
- Product reliability results valid for  $T_J \leq 150^\circ\text{C}$  (recommended  $T_{J,op} = -40 \dots +150^\circ\text{C}$ )
- Temperature sensor: No basic insulation to main circuit, max. potential difference 850V to -DC

| Characteristics           |  |   |               |              |               |
|---------------------------|--|---|---------------|--------------|---------------|
| Symbol                    | Conditions   | min.  | typ.          | max.         | Unit          |
| <b>Inverter - IGBT</b>    |  |   |               |              |               |
| $Q_G$                     | $V_{GE} = -8 \text{ V} \dots +15 \text{ V}$  |   | 45            |              | nC            |
| $R_{Gint}$                | $T_J = 25^\circ\text{C}$   |   | 0             |              | $\Omega$      |
| $t_{d(on)}$               | $V_{CC} = 600 \text{ V}$<br>$I_C = 8 \text{ A}$  | $T_J = 150^\circ\text{C}$                             | 32            |              | ns            |
| $t_r$                     | $R_{G on} = 47 \Omega$   | $T_J = 150^\circ\text{C}$                             | 34            |              | ns            |
| $E_{on}$                  | $R_{G off} = 47 \Omega$  | $T_J = 150^\circ\text{C}$                             | 0.9           |              | mJ            |
| $t_{d(off)}$              |  | $T_J = 150^\circ\text{C}$                             | 295           |              | ns            |
| $t_f$                     |  | $T_J = 150^\circ\text{C}$                             | 68            |              | ns            |
| $E_{off}$                 | $V_{GE} = +15/-15 \text{ V}$   | $T_J = 150^\circ\text{C}$                             | 0.7           |              | mJ            |
| $R_{th(j-s)}$             | per IGBT, $\lambda_{paste}=0.8 \text{ W}/(\text{K}\cdot\text{m})$  |   | 1.84          |              | K/W           |
| <b>Inverse - Diode</b>    |  |   |               |              |               |
| $V_F = V_{EC}$            | $I_F = 8 \text{ A}$<br>$V_{GE} = 0 \text{ V}$<br>chipelevel  | $T_J = 25^\circ\text{C}$<br>$T_J = 150^\circ\text{C}$ | 2.33<br>2.35  | 2.65<br>2.68 | V             |
| $V_{F0}$                  | chipelevel   | $T_J = 25^\circ\text{C}$<br>$T_J = 150^\circ\text{C}$ | 1.30<br>0.90  | 1.50<br>1.10 | V             |
| $r_F$                     | chipelevel   | $T_J = 25^\circ\text{C}$<br>$T_J = 150^\circ\text{C}$ | 129<br>181    | 144<br>198   | m $\Omega$    |
| $I_{RRM}$                 | $I_F = 8 \text{ A}$  | $T_J = 150^\circ\text{C}$                             | 7.7           |              | A             |
| $Q_{rr}$                  | $V_{GE} = -15 \text{ V}$<br>$V_{CC} = 600 \text{ V}$   | $T_J = 150^\circ\text{C}$                             | 1.23          |              | $\mu\text{C}$ |
| $E_{rr}$                  | $di/dt_{off} = 335 \text{ A}/\mu\text{s}$  | $T_J = 150^\circ\text{C}$                             | 0.5           |              | mJ            |
| $R_{th(j-s)}$             | per Diode, $\lambda_{paste}=0.8 \text{ W}/(\text{K}\cdot\text{m})$   |   | 2.53          |              | K/W           |
| <b>Rectifier - Diode</b>  |  |   |               |              |               |
| $V_F = V_{EC}$            | $I_F = 8 \text{ A}$<br>chipelevel  | $T_J = 25^\circ\text{C}$<br>$T_J = 125^\circ\text{C}$ | 1.00<br>0.90  | 1.21<br>1.10 | V             |
| $V_{F0}$                  | chipelevel   | $T_J = 25^\circ\text{C}$<br>$T_J = 125^\circ\text{C}$ | 0.88<br>0.73  | 0.98<br>0.83 | V             |
| $r_F$                     | chipelevel   | $T_J = 25^\circ\text{C}$<br>$T_J = 125^\circ\text{C}$ | 15<br>21      | 29<br>34     | m $\Omega$    |
| $R_{th(j-s)}$             | per Diode, $\lambda_{paste}=0.8 \text{ W}/(\text{K}\cdot\text{m})$   |   | 1.5           |              | K/W           |
| <b>Module</b>             |  |   |               |              |               |
| $M_s$                     | to heat sink   | 2   |               | 2.5          | Nm            |
| $W$                       |  |   | 20            |              | g             |
| <b>Temperature Sensor</b> |  |   |               |              |               |
| $R_{100}$                 | $T_r = 100^\circ\text{C}$ , tolerance = 3 %  |   | 1670 $\pm$ 3% |              | $\Omega$      |
| $R_{(T)}$                 | $R_{(T)} = 1000\Omega [1 + A(T - 25^\circ\text{C}) + B(T - 25^\circ\text{C})^2]$<br>, $A = 7.635 \cdot 10^{-3} \text{ }^\circ\text{C}^{-1}$ ,<br>$B = 1.731 \cdot 10^{-5} \text{ }^\circ\text{C}^{-2}$ |   |               |              |               |



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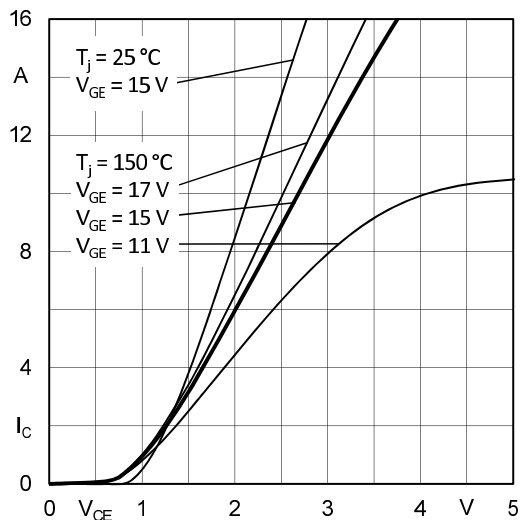


Fig. 1: Typ. output characteristic

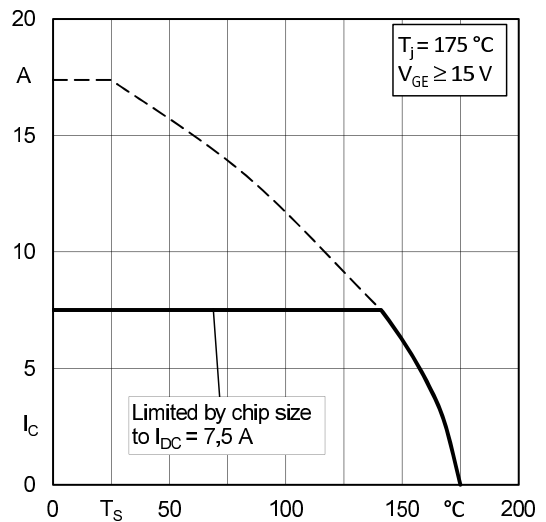


Fig. 2: Typ. rated current vs. temperature  $I_C = f(T_S)$

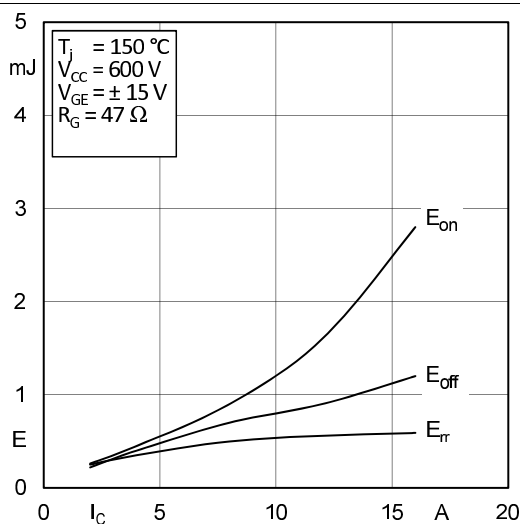


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

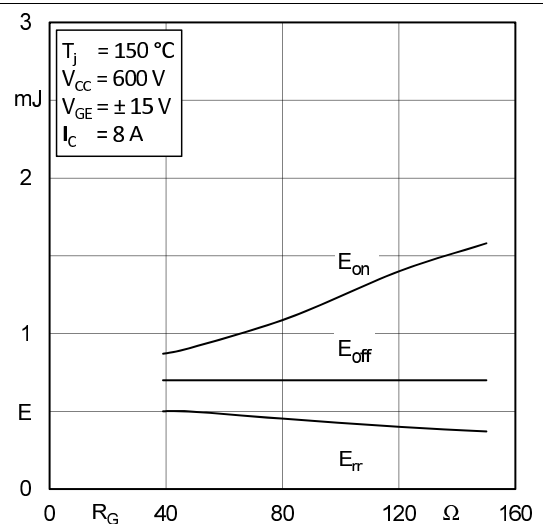


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

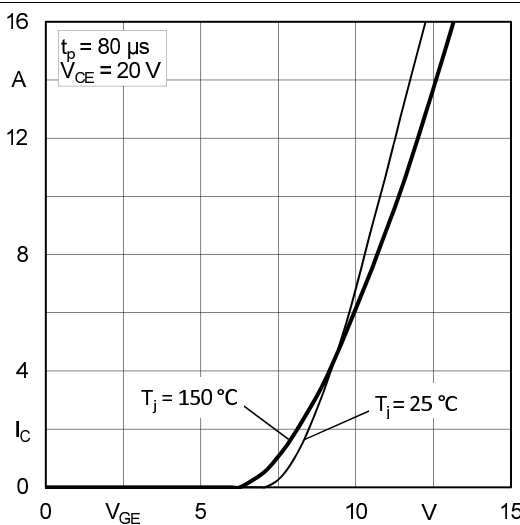


Fig. 5: Typ. transfer characteristic

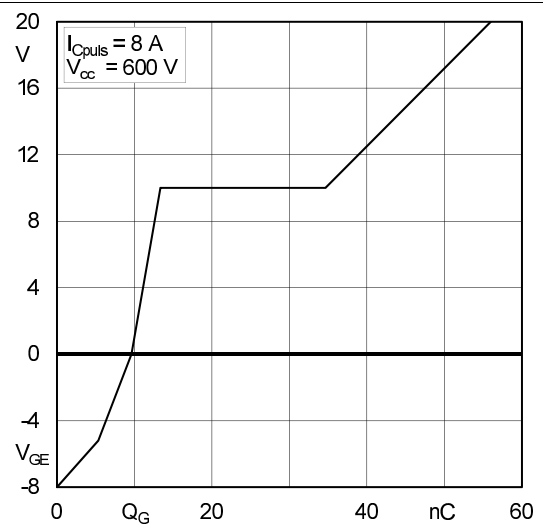
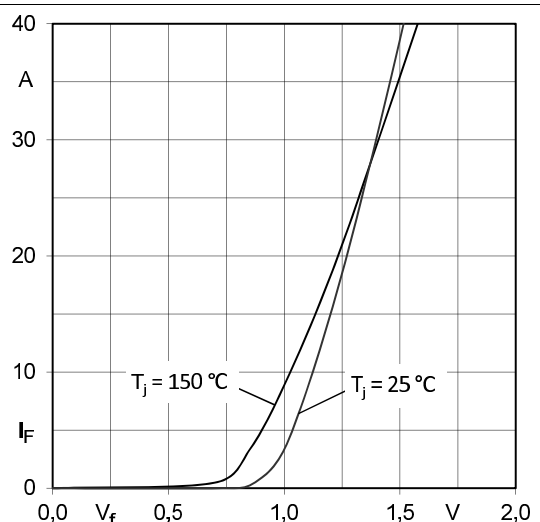
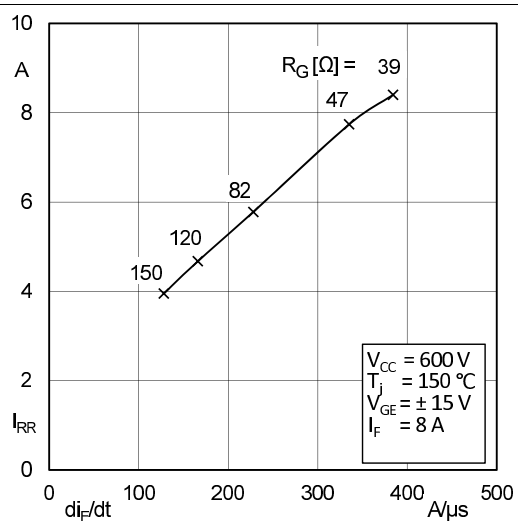
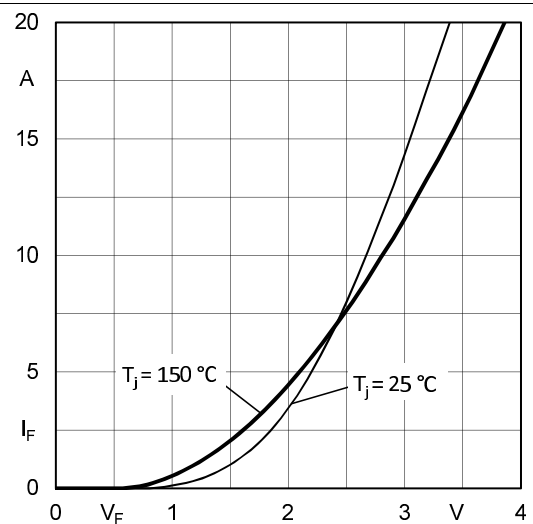
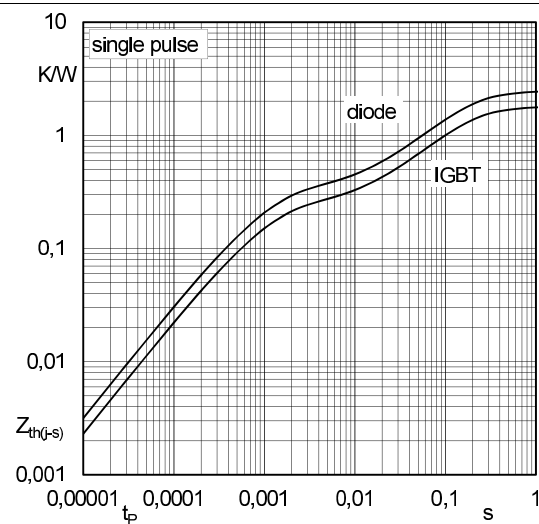
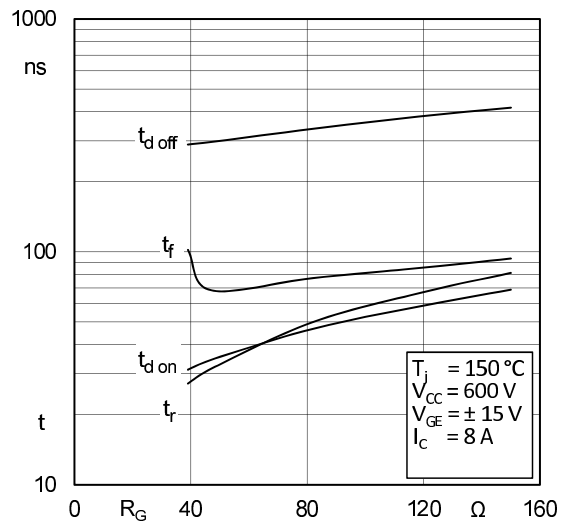
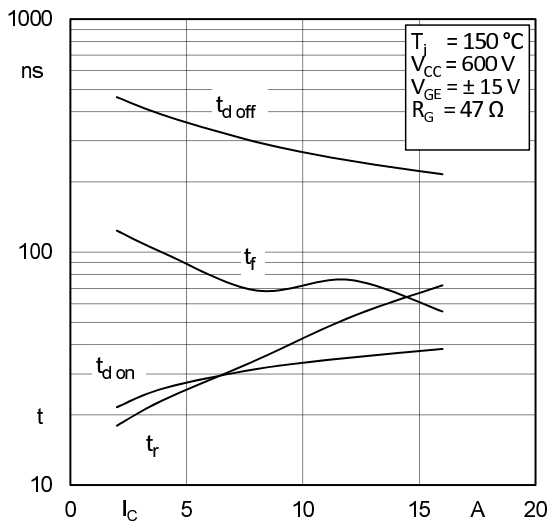
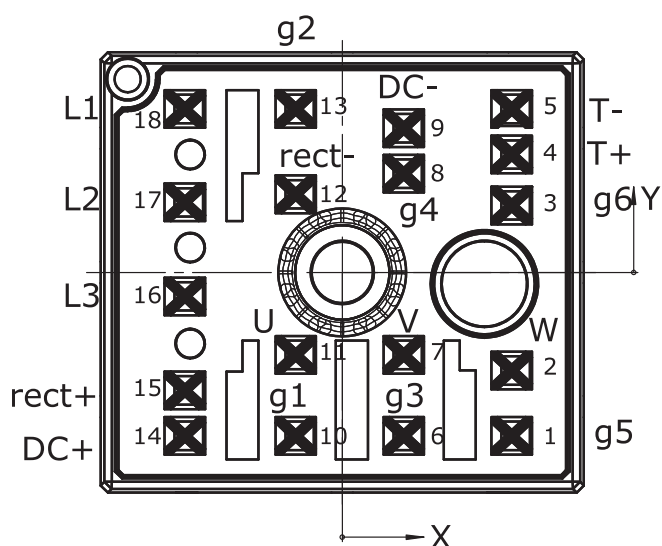


Fig. 6: Typ. gate charge characteristic

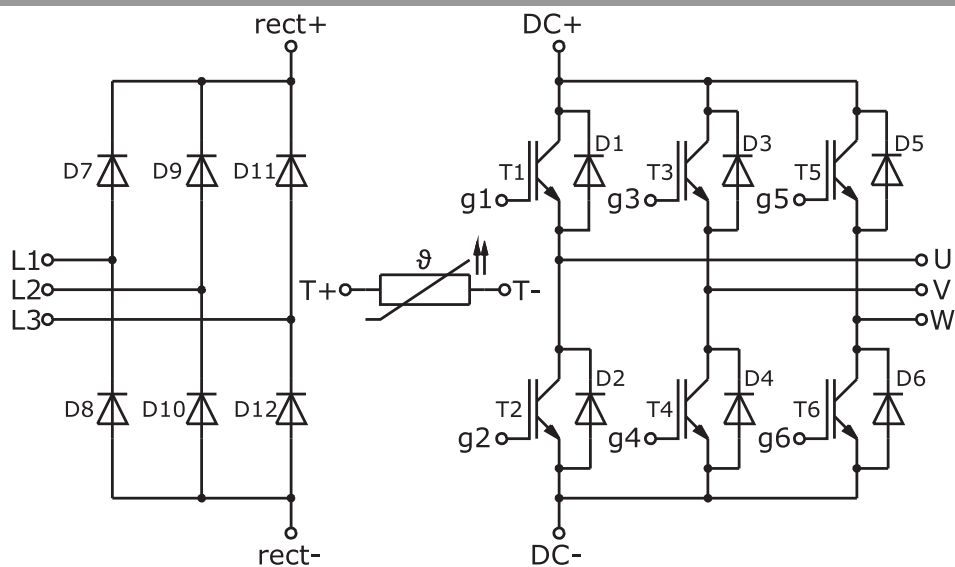


| Pin out |       |        |          |     |        |        |          |
|---------|-------|--------|----------|-----|--------|--------|----------|
| Pin     | X     | Y      | Function | Pin | X      | Y      | Function |
| 1       | 11,93 | -11,50 | g5       | 10  | -3,28  | -11,50 | g1       |
| 2       | 11,93 | -6,90  | W        | 11  | -3,28  | -5,80  | U        |
| 3       | 11,93 | 4,71   | g6       | 12  | -3,28  | 5,50   | rect-    |
| 4       | 11,93 | 8,3    | T+       | 13  | -3,28  | 11,50  | g2       |
| 5       | 11,93 | 11,50  | T-       | 14  | -11,08 | -11,50 | DC+      |
| 6       | 4,33  | -11,50 | g3       | 15  | -11,08 | -8,30  | rect+    |
| 7       | 4,33  | -5,80  | V        | 16  | -11,08 | -1,68  | L3       |
| 8       | 4,33  | 6,95   | g4       | 17  | -11,08 | 4,93   | L2       |
| 9       | 4,33  | 10,15  | DC-      | 18  | -11,08 | 11,50  | L1       |

all values in mm



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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